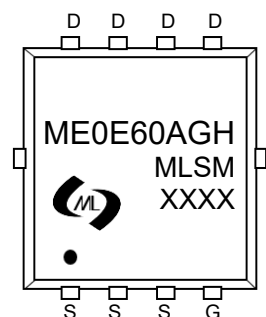


Features

- High density cell design for ultra low $R_{DS(on)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Load switching
- Hard switched and high frequency circuits
- Uninterruptible power supply

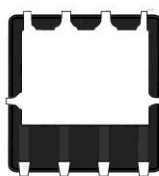


Marking and pin assignment

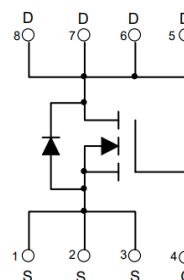
ME0E60AGH : Device code
 XXXX : Code

Product Summary

V_{DS}	$R_{DS(ON)}$	I_D
40V	6mΩ@10V	60A



PDFN3X3-8L view



Schematic diagram



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)			
V_{DS}	Drain-Source Breakdown Voltage	40	V
V_{GS}	Gate-Source Voltage	±20	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-50 to 155	°C
I_S	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$ 60	A
Mounted on Large Heat Sink			
I_{DM}	Pulse Drain Current Tested	$T_C=25^\circ\text{C}$ 240	A
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$ 60	A
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$ 28	W
$R_{\theta JA}$	Thermal Resistance Junction-to-Ambient	55	°C/W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
ME0E60AGH	PDFN3X3-8L	ME0E60AGH	5,000	10,000	70,000	13"reel

Electrical Characteristics (TJ=25℃ unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25℃ (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	40	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =40V, V _{GS} =0V	--	--	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	2.0	3.0	4.0	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =20A	--	4.3	6.0	mΩ
Dynamic Electrical Characteristics @ TJ = 25℃ (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1MHz	--	1171	--	pF
C _{OSS}	Output Capacitance		--	344	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	21	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DD} =20V, I _D =35A, V _{GS} =10V	--	19.3	--	nC
Q _{gs}	Gate Source Charge		--	8.22	--	nC
Q _{gd}	Gate Drain Charge		--	3.5	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =20V, I _D =35A, V _{GS} =10V, R _G =3Ω	--	9.2	--	nS
t _r	Turn-on Rise Time		--	6.8	--	nS
t _{d(off)}	Turn-Off Delay Time		--	22.5	--	nS
t _f	Turn-Off Fall Time		--	14.3	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	TJ=25℃, Is=10A	--	--	1.2	V

Typical Operating Characteristics

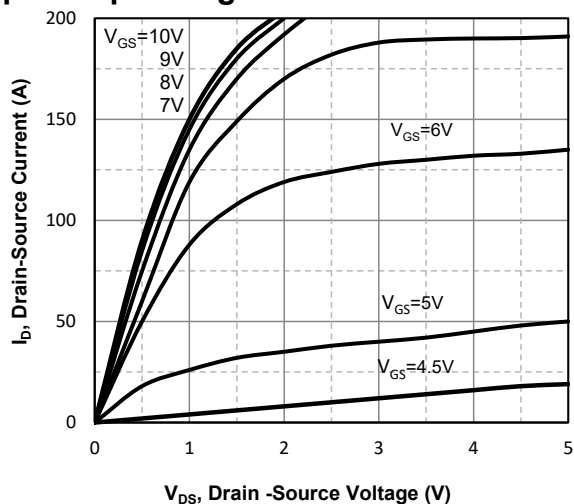


Fig1. Typical Output Characteristics

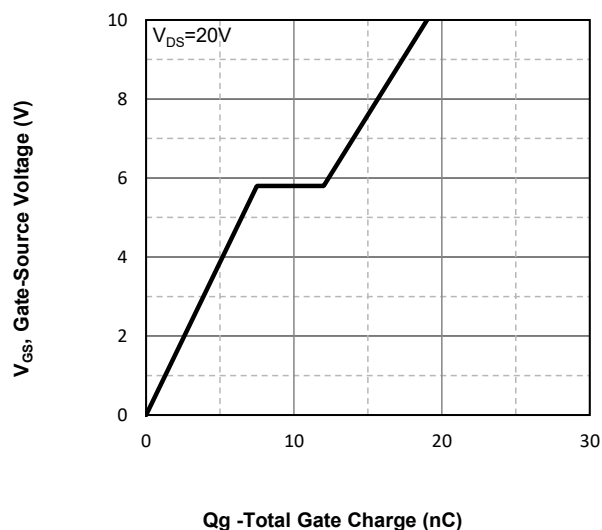


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

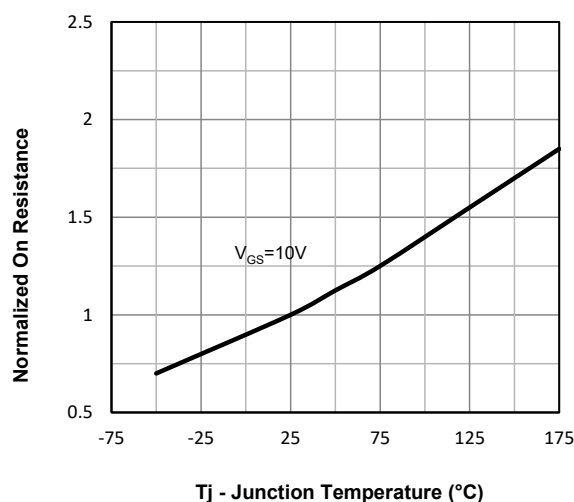


Fig3. Normalized On-Resistance Vs. Temperature

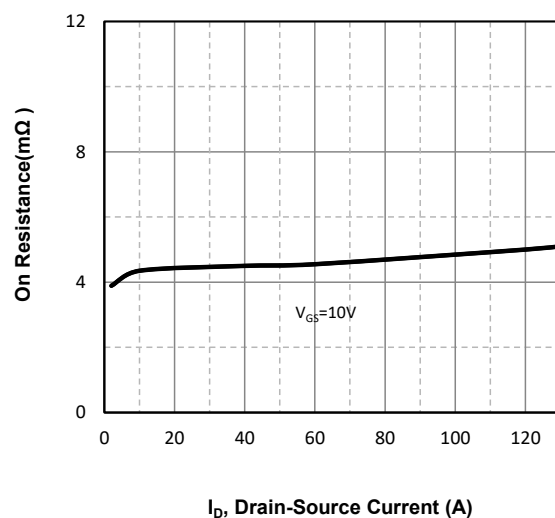


Fig4. On-Resistance Vs. Drain-Source Current

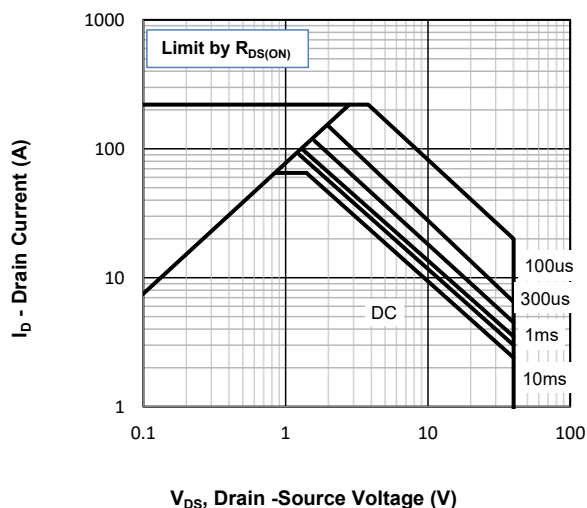


Fig5. Maximum Safe Operating Area

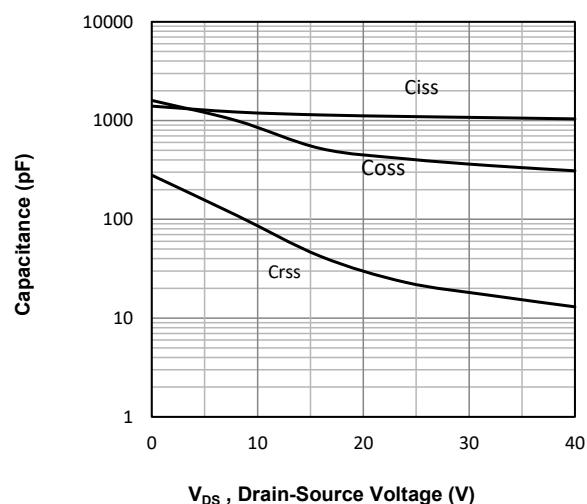
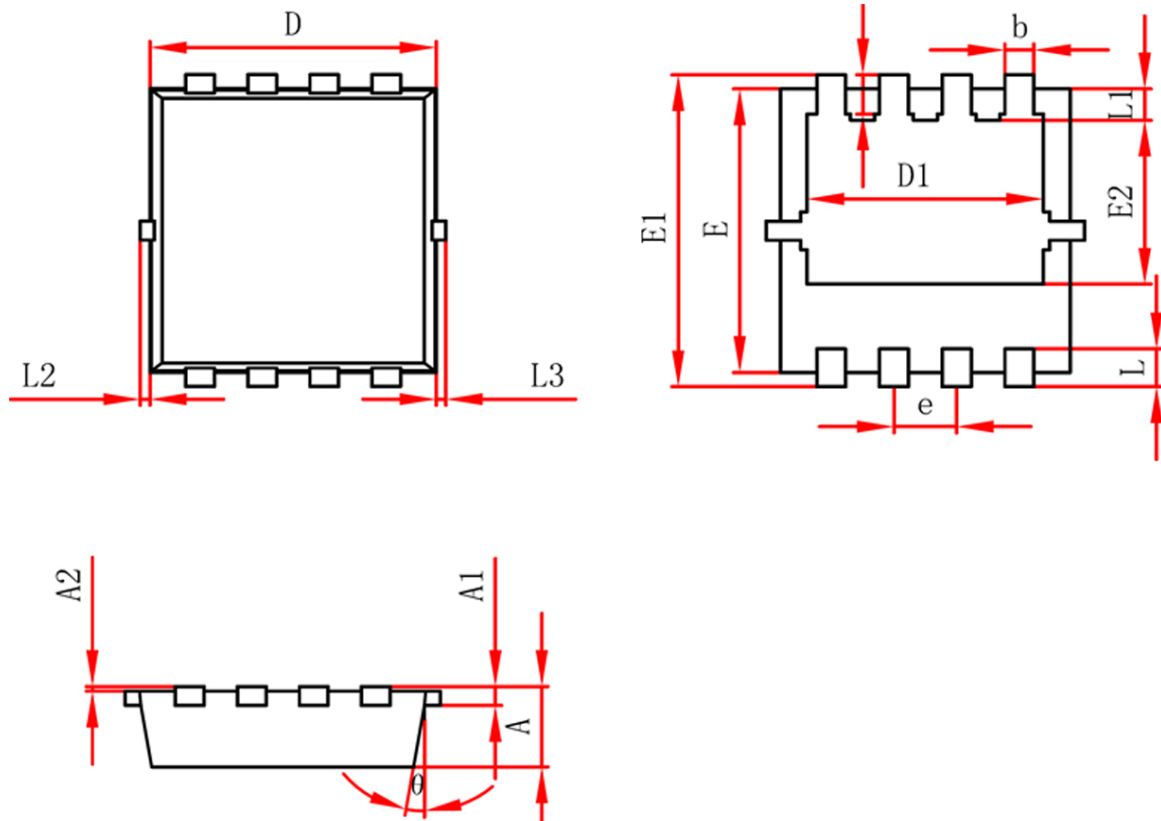


Fig6 Typical Capacitance Vs. Drain-Source

PDFN3X3-8L Package information


Symbol	Dimensions in Millimeters(mm)		Dimensions in Inches	
	Min	Max	Min	Max
A	0.750	0.850	0.030	0.034
A1	0.152 REF.		0.006 REF.	
A2	0~0.05		0~0.002	
D	2.950	3.150	0.117	0.125
D1	2.400	2.500	0.095	0.099
E	2.950	3.050	0.117	0.121
E1	3.250	3.350	0.129	0.132
E2	1.685	1.785	0.067	0.071
b	0.250	0.350	0.010	0.014
e	0.600	0.700	0.024	0.028
L	0.350	0.450	0.014	0.018
L1	0.325	0.425	0.013	0.017
L2	0~0.100		0~0.004	
L3	0~0.100		0~0.004	
H	0.365	0.465	0.014	0.018
θ	10°	12°	10°	12°